

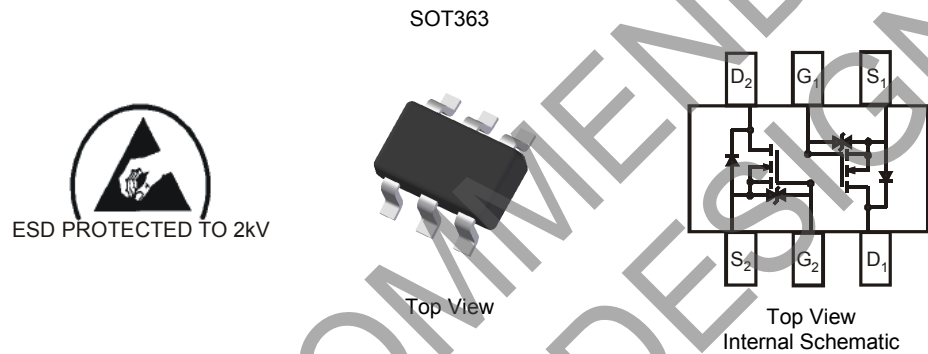
**DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

**Features**

- Dual N-Channel MOSFET
- Low On-Resistance (1.0V Max)
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **ESD Protected up to 2kV**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound.  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Alloy 42  
Leadframe. Solderable per MIL-STD-202, Method 208<sup>③</sup>
- Weight: 0.006 grams (Approximate)



**Ordering Information (Note 4)**

Part Number	Case	Packaging
DMN5L06DWK-7	SOT363	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**



DAB = Marking Code  
YM = Date Code Marking  
Y = Year ex: G = 2019  
M = Month ex: 9 = September

**Date Code Key**

Year	2006	2007	2008	...	2012	2013	2014	2015	2016	2017	2018	2019
Code	T	U	V	...	Z	A	B	C	D	E	F	G
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current	I <sub>D</sub>	305 800	mA
		Continuous Pulsed (Note 6)	

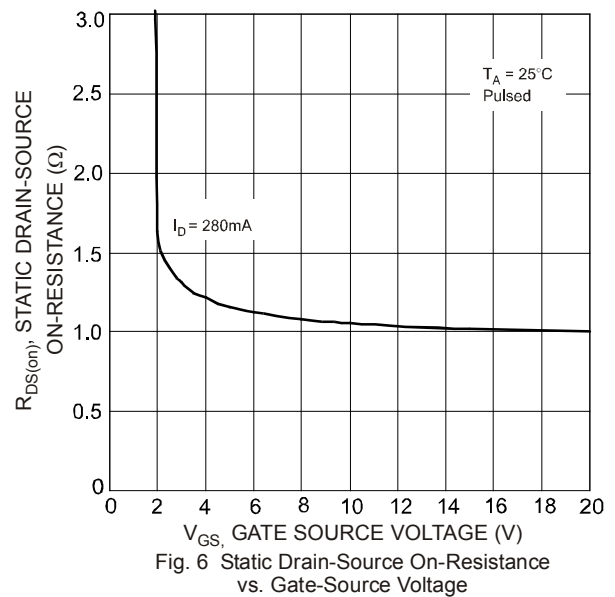
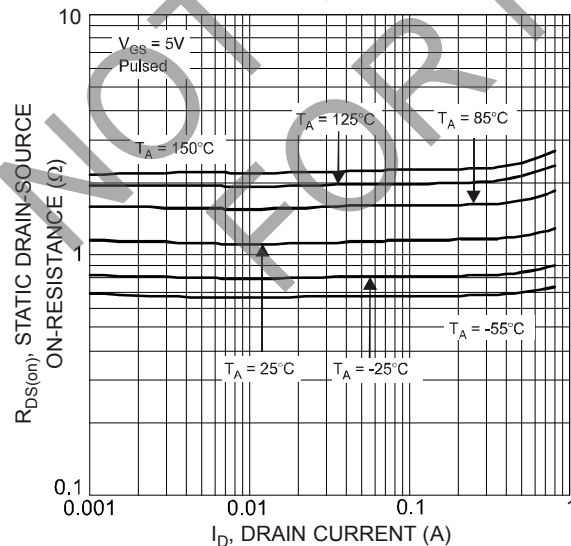
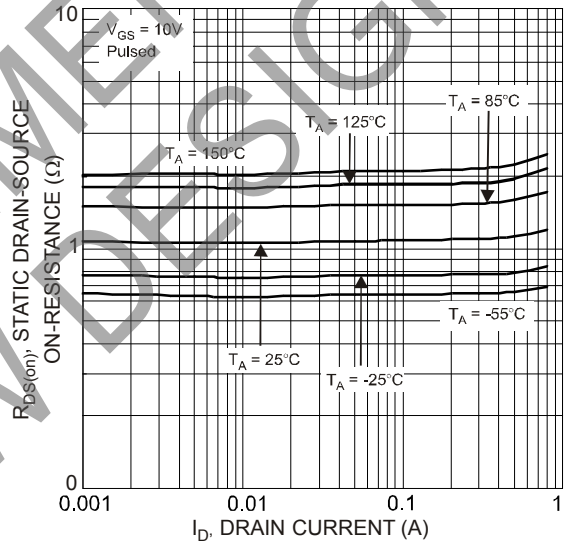
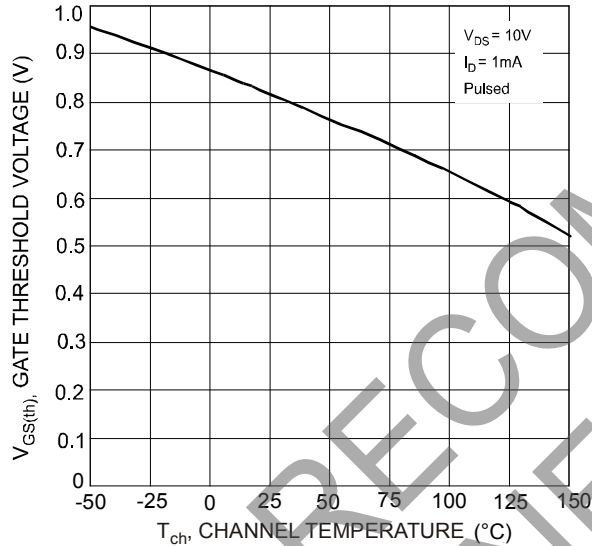
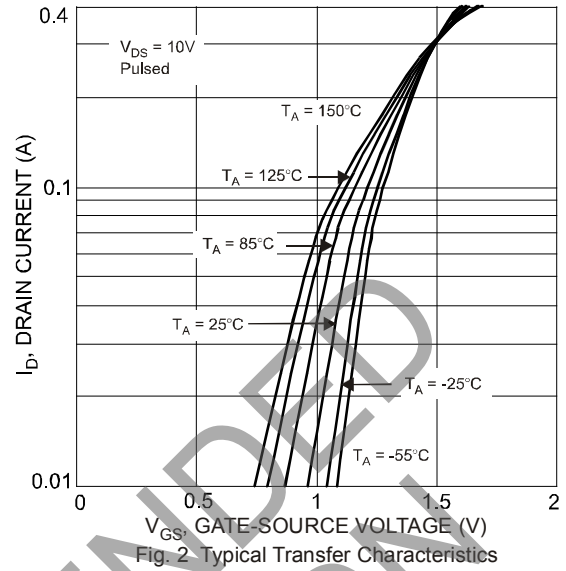
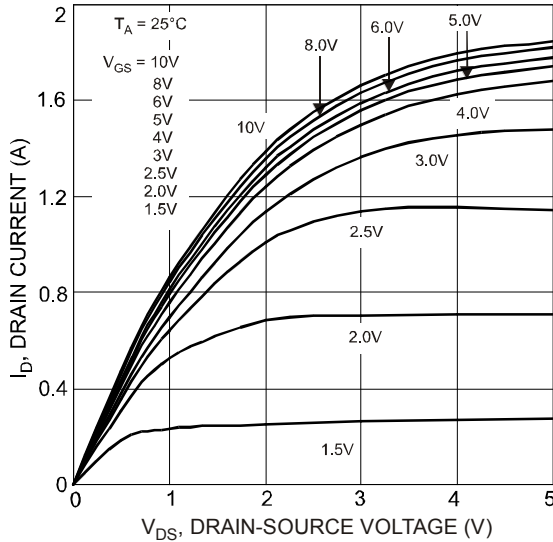
### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	250	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	500	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	50	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	60	nA	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	1 500 50	μA nA nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V V <sub>GS</sub> = ±5V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.49	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	—	3.0 2.5 2.0	Ω	V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 50mA V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 50mA V <sub>GS</sub> = 5.0V, I <sub>D</sub> = 50mA
On-State Drain Current	I <sub>D(ON)</sub>	0.5	1.4	—	A	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 7.5V
Forward Transconductance	Y <sub>FS</sub>	200	—	—	mS	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.2A
Source-Drain Diode Forward Voltage	V <sub>SD</sub>	0.5	—	1.4	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	—	50	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	—	5.0	pF	
Gate Resistance	R <sub>G</sub>	—	65	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>G</sub>	—	0.4	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.25A
Gate-Source Charge	Q <sub>GS</sub>	—	0.1	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	0.1	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.1	—	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 25Ω, I <sub>D</sub> = 0.2A
Turn-On Rise Time	t <sub>R</sub>	—	1.8	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	14.4	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	8.4	—	ns	

- Notes:
- Device mounted on FR-4 PCB.
  - Pulse width ≤10μs, Duty Cycle ≤1%.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.



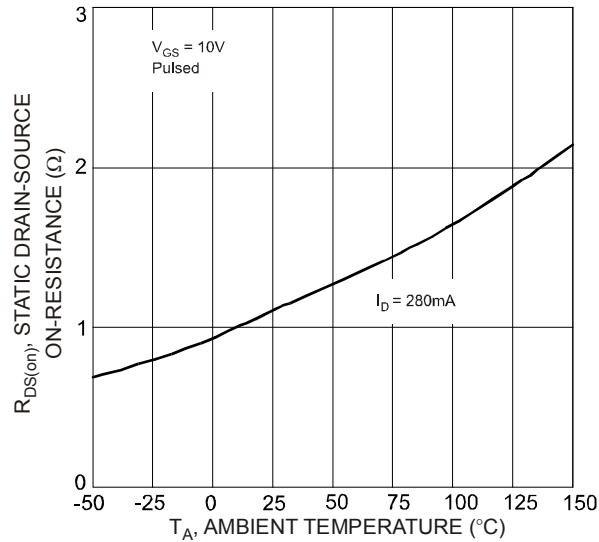


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

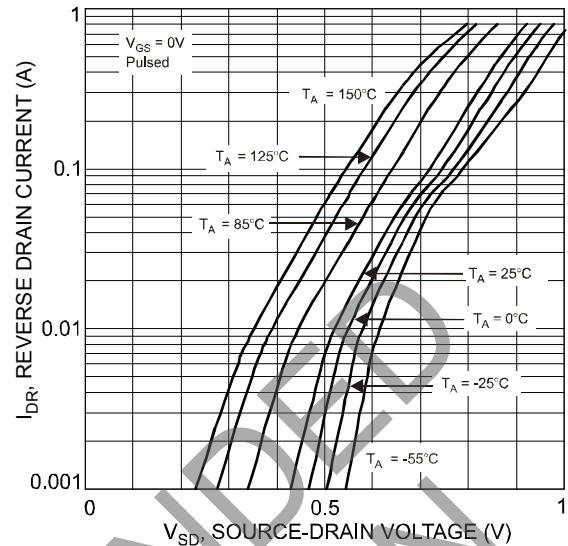


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

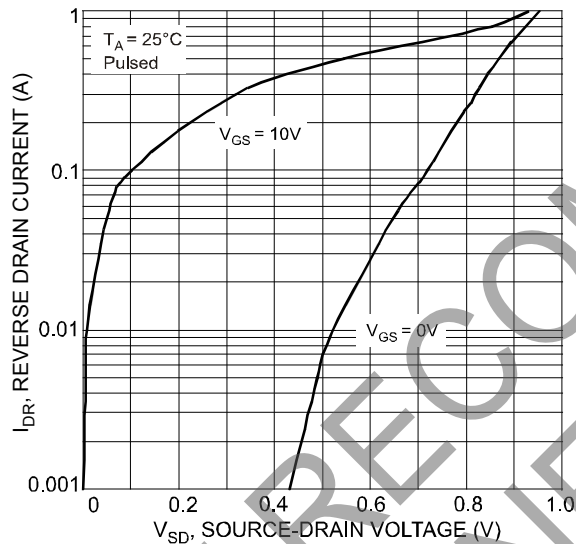


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

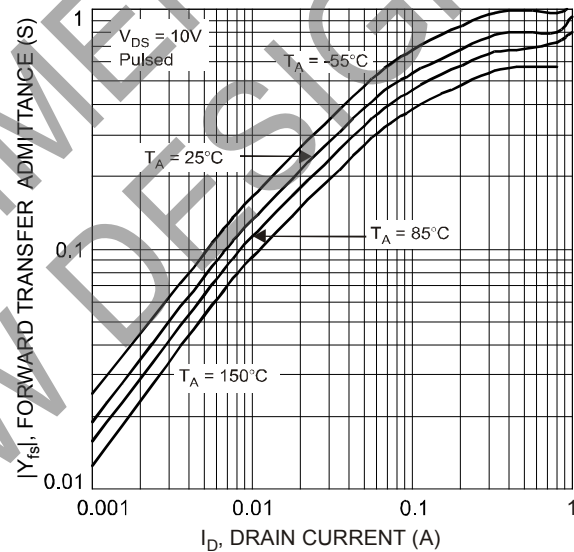


Fig. 10 Forward Transfer Admittance vs. Drain Current

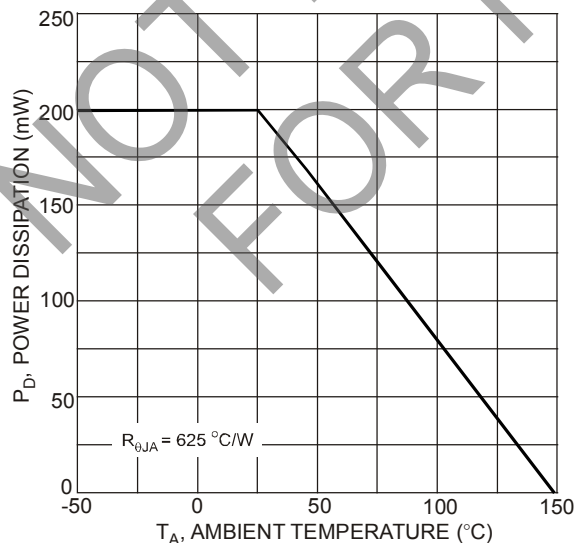
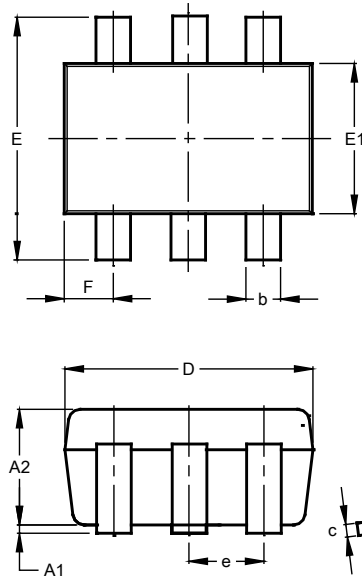


Fig. 11 Derating Curve - Total

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT363

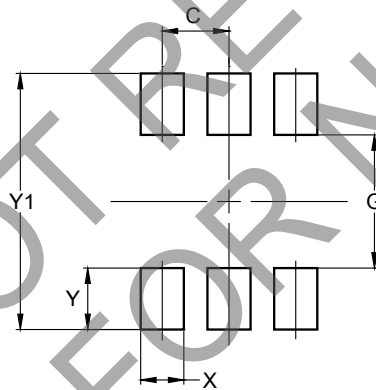


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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